Oral presentation | 13 Semiconductors | 13.8 Compound and power electron devices and process technology

[14a-B1-1~1]13.8 Compound and power electron devices and process technology

Seiji Nakamura(TMU)

Wed. Sep 14, 2016 11:45 AM - 12:15 PM B1 (Exhibition Hall)

 \triangle : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼: Both of Above

No Mark: None of Above

11:45 AM - 12:15 PM

[14a-B1-1][JSAP Paper Award Speech] Characterization of electronic states at insulator/(AI)GaN interfaces for improved insulated gate and surface passivation structures of GaN-based transistors

OZenji Yatabe¹, Yujin Hori², Wancheng Ma³, Joel T. Asubar⁴, Masamichi Akazawa³, Taketomo Sato³, Tamotsu Hashizume³ (1.Kumamoto Univ., 2.Furukawa Electric, 3.Hokkaido Univ., 4.Fukui Univ.) Keywords: JSAP Paper Award